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(54) Title: CONTROL OF METALLIC CONTAMINATION FROM METAL-CONTAINING PHOTORESIST

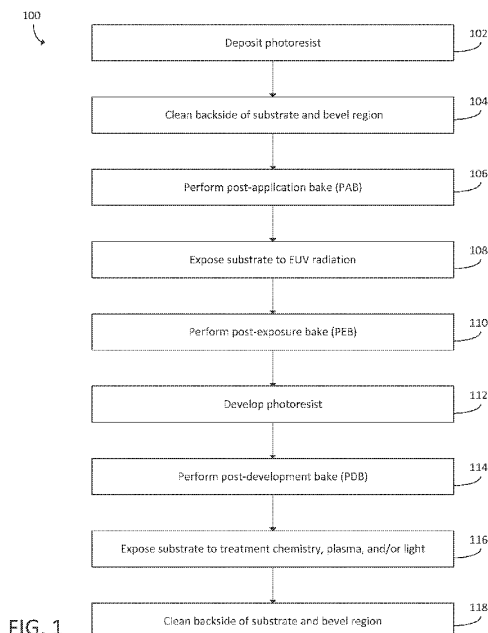


FIG. 1

(57) Abstract: Various techniques for controlling metal-containing contamination on a semiconductor substrate are provided herein. Such techniques may involve one or more of a post-development bake treatment, a chemical treatment, a plasma treatment, a light treatment, and a backside and bevel edge clean. The techniques may be combined as desired for a particular application. In many cases, the techniques are used to address metal-containing contamination that is generated during a photoresist development operation.

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